

ALPHANUMERIC INDEX — CROSS-REFERENCE (Continued)

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2N6059JTX	2N6059JTX		3-143	2N6235		2N3585	3-20
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2N6107	2N6107		3-151	2N6254		2N5878	3-120
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2N6109	2N6109		3-151	2N6258		2N5686	3-112
2N6110		2N6111	3-151	2N6259		2N5631	3-105
2N6111	2N6111		3-151	2N6260		2N3054A	3-2
2N6121	2N6121		3-154	2N6261		2N4233A	3-64
2N6122	2N6122		3-154	2N6262		2N5760	3-116
2N6123	2N6123		3-154	2N6263		2N3584	3-20
2N6124	2N6124		3-154	2N6264		2N3584	3-20
2N6125	2N6125		3-154	2N6270		2N6338	3-188
2N6126		TIP32C	3-1073	2N6271		2N6338	3-188
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2N6132		TIP42C	3-1083	2N6274JTXV	2N6274JTXV		3-168
2N6133		TIP42C	3-1083	2N6275	2N6275		3-168
2N6134		TIP42C	3-1083	2N6276		2N6275	3-168
2N6175		MPS-U10	3-1052	2N6277	2N6277		3-168
2N6176		MPS-U10	3-1052	2N6277JAN	2N6277JAN		3-168
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*Consult Motorola if a direct replacement is necessary.

TABLE 1 — METAL TO-204, TO-204AE (continued)

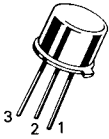
I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		h _{FE} Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp		
50	200	BUS51●		15 min	50					350
	400	MJ10015●##		10 min	40	2.5	1	20		250
	500	BUT34●## MJ10016●##		15 min 10 min	32 40	3 2.5	1.5 1	32 20		250 250
56	400	BUT33●##		20 min	36	3.3	1.6	36		250
60	60	MJ14000●	MJ14001●	15/100	50					300
	80	MJ14002●	MJ14003●	15/100	50					300
	200	MJ10020●##		75 min	15	3.5	0.5	30		250
	250	MJ10021●##		75 min	15	3.5	0.5	30		250
70	125	BUS50●		15 min	50					350

● Modified TO-3, 60 mil pins, # |h_{FE}| @ 1 MHz, ## Darlington

TABLE 2 — METAL TO-205 (Formerly TO-39)



STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR
(Pin 3 connected to case)



CASE 79-04 (TO-205AD)

I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		h _{FE} Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp		
0.5	300		MJ4646	20 min	0.5	0.72*		0.05	40	5
	400		MJ4647	20 min	0.5	0.72*		0.05	30	5
3	40		2N3719 2N3867	25/180 40/200	1 1.5	0.4* 0.4*		1 1.5	60 60	6 6
	60		2N3720 2N3868	25/180 30/150	1 1.5	0.4* 0.4*		1 1.5	60 60	6 6
	80		2N6303	30/150	1.5	0.4*		1.5	60	6
4	60	2N4877		20/100	4	1.5	0.5	4	4	10
5	80	2N5336 2N5337	2N6190 2N6191	30/120 60/240	2 2	2 2	0.2 0.2	2 2	30 30	6 6
	100	2N5338 2N5339	2N6193	30/120 60/240	2 2	2 2	0.2 0.2	2 2	30 30	10 6

JAN, JTX, JTXV Available

*t_{off}

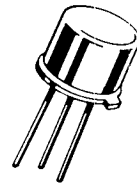
5 AMPERE

POWER TRANSISTORS

PNP SILICON

- 80-100 VOLTS**
10 WATTS

Rating	Symbol	2N6190 2N6191	2N6193	Unit
Collector-Emitter Voltage	V_{CE0}	80	100	Vdc
Collector-Base Voltage	V_{CB}	80	100	Vdc
Emitter-Base Voltage	V_{EB}	6.0		Vdc
Collector Current – Continuous	I_C	5.0		Adc
Base Current	I_B	1.0		Adc
Total Device Dissipation @ $T_C = 25^{\circ}C$	P_D	10		Watts
Derate above $25^{\circ}C$		57.1		mW/ $^{\circ}C$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$



Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	17.5	$^{\circ}\text{C/W}$

STYLE 1:
 PIN 1 EMITTER
 2 BASE
 3 COLLECTOR

⌀	⌀ 0.38	0.014	⌀	T	A	⌀	H	⌀
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A line graph showing the relationship between Power Dissipation (P_D) in Watts and Case Temperature (T_C) in degrees Celsius for the 2N3638 JFET. The y-axis represents P_D and ranges from 0 to 10 Watts with major grid lines every 2 units and minor grid lines every 1 unit. The x-axis represents T_C and ranges from 0 to 200 degrees Celsius with major grid lines every 40 units and minor grid lines every 20 units. The graph shows a constant power dissipation of 10 Watts for temperatures up to approximately 25°C. Beyond 25°C, the power dissipation decreases linearly, reaching 0 Watts at 200°C.

T_C (°C)	P_D (Watts)
0	10
25	10
50	9
75	8
100	7
125	6
150	5
175	4
200	0

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.51	9.39	0.335	0.370
B	7.75	8.50	0.305	0.335
C	6.10	6.60	0.240	0.260
D	0.41	0.53	0.016	0.021
E	0.23	0.14	0.009	0.004
F	0.41	0.48	0.016	0.019
G	5.00 BSC		0.200 BSC	
H	0.72	0.86	0.028	0.034
J	0.74	1.14	0.029	0.045
K	12.70	19.05	0.500	0.750
L	6.35	—	0.250	—
M	45° BSC		45° BSC	
P	—	1.27	—	0.050
R	2.54	—	0.100	—

**CASE 79-04
TO-205AD
(TO-39)**

2N6190, 2N6191, 2N6193

* ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (1) ($I_C = 50 \text{ mA}$, $I_B = 0$)	$V_{CE(sus)}$	80 100	— —	Vdc
Collector Cutoff Current ($V_{CE} = 75 \text{ Vdc}$, $I_B = 0$) ($V_{CE} = 90 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	— —	100 100	μAdc
Collector Cutoff Current ($V_{CE} = 75 \text{ Vdc}$, $V_{BE(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 90 \text{ Vdc}$, $V_{BE(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = 75 \text{ Vdc}$, $V_{BE(off)} = 1.5 \text{ Vdc}$, $T_C = 150^\circ\text{C}$) ($V_{CE} = 90 \text{ Vdc}$, $V_{BE(off)} = 1.5 \text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	— — — —	10 10 1.0 1.0	μAdc mAdc
Collector Cutoff Current ($V_{CB} = 80 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	— —	10 10	μAdc
Emitter Cutoff Current ($V_{BE} = 6.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	100	μAdc
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 500 \text{ mA}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 2.0 \text{ A}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 5.0 \text{ A}$, $V_{CE} = 2.0 \text{ Vdc}$)	h_{FE}	30 60 30 60 20 40	— — 120 240 — —	—
Collector-Emitter Saturation Voltage ($I_C = 2.0 \text{ A}$, $I_B = 0.2 \text{ A}$) ($I_C = 5.0 \text{ A}$, $I_B = 0.5 \text{ A}$)	$V_{CE(sat)}$	— —	0.7 1.2	Vdc
Base-Emitter Saturation Voltage ($I_C = 2.0 \text{ A}$, $I_B = 0.2 \text{ A}$) ($I_C = 5.0 \text{ A}$, $I_B = 0.5 \text{ A}$)	$V_{BE(sat)}$	— —	1.2 1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain-Bandwidth Product (2) ($I_C = 0.5 \text{ A}$, $V_{CE} = 10 \text{ Vdc}$, $f_{Test} = 10 \text{ MHz}$)	f_T	30	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 100 \text{ kHz}$)	C_{ob}	—	300	pF
Input Capacitance ($V_{BE} = 2.0 \text{ Vdc}$, $I_C = 0$, $f = 100 \text{ kHz}$)	C_{ib}	—	1250	pF
SWITCHING CHARACTERISTICS				
Delay Time ($V_{CC} = 40 \text{ Vdc}$, $V_{BE(off)} = 3.0 \text{ Vdc}$, $I_C = 2.0 \text{ A}$, $I_B = 0.2 \text{ A}$)	t_d	—	100	ns
Rise Time ($V_{CC} = 40 \text{ Vdc}$, $I_C = 2.0 \text{ A}$, $I_B = 0.2 \text{ A}$)	t_r	—	100	ns
Storage Time ($V_{CC} = 40 \text{ Vdc}$, $I_C = 2.0 \text{ A}$, $I_B = 0.2 \text{ A}$)	t_s	—	2.0	μs
Fall Time ($I_B = 0.2 \text{ A}$)	t_f	—	200	ns

* Indicates JEDEC Registered Data

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

(2) $f_T = 1/h_{FE} \cdot f_{Test}$

FIGURE 2 — SWITCHING TIME TEST CIRCUIT

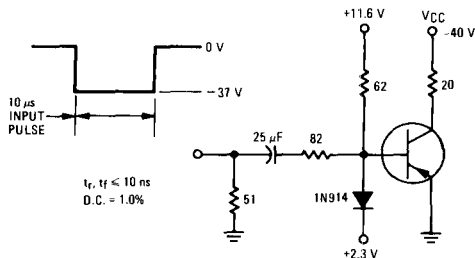
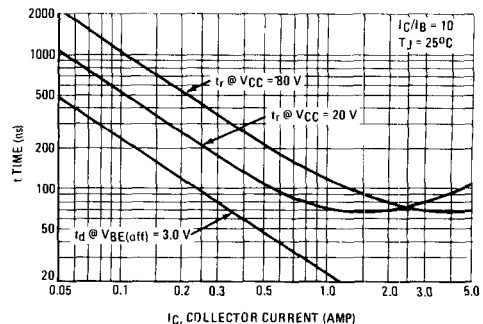


FIGURE 3 — TURN ON TIME



2N6190, 2N6191, 2N6193

FIGURE 4 – THERMAL RESPONSE

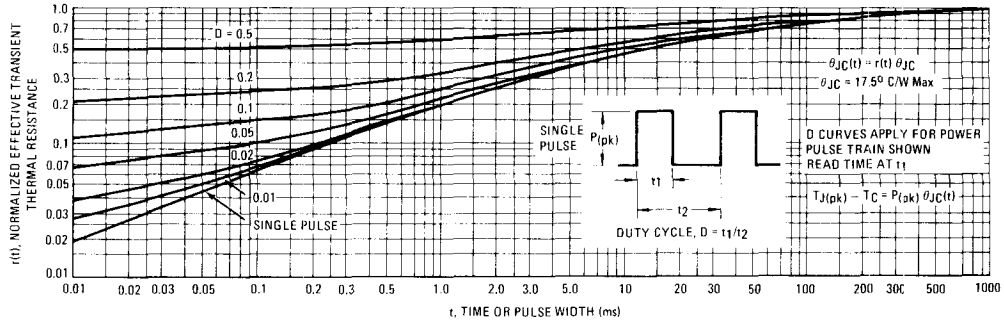
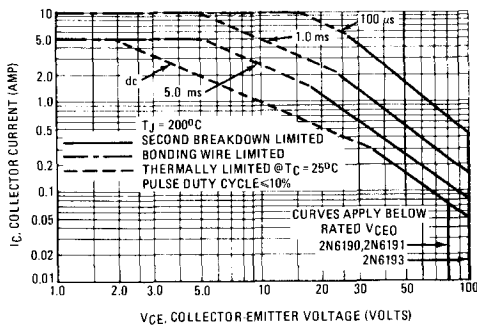


FIGURE 5 – ACTIVE-REGION SAFE OPERATING AREA



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_J(pk) = 200^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_J(pk) < 200^\circ\text{C}$. $T_J(pk)$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

FIGURE 6 – TURN-OFF TIME

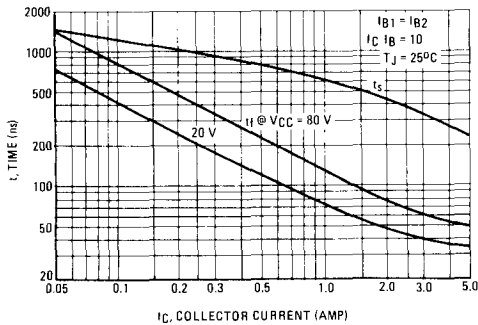


FIGURE 7 – CAPACITANCE versus VOLTAGE

